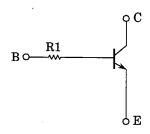
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

RN1970,RN1971

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- Including two devices in US6 (ultra super mini type 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN2970~RN2971

Equivalent Circuit

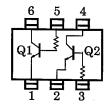


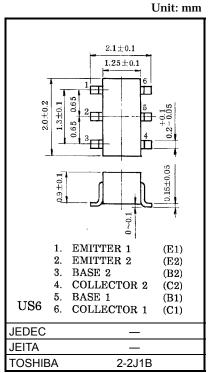
Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characterisstic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	IC	100	mA
Collector power dissipation	P _C *	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C

^{*:} Total rating

Equivalent Circuit (Top View)





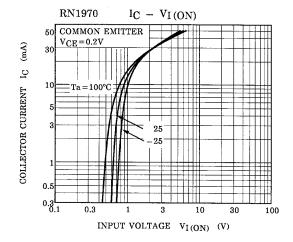
Weight: 6.8mg(typ.)

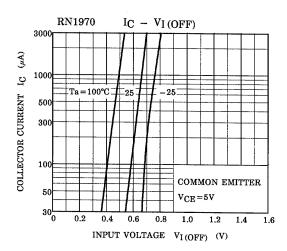


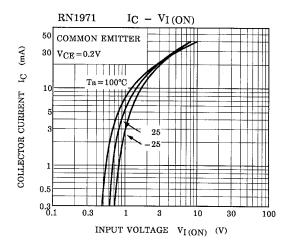
Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

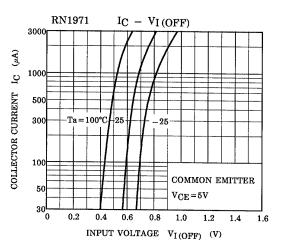
Characteristic		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	_	V _{CB} = 5V, I _E = 0	_	_	100	nA
Emitter cut-off current		I _{EBO}	_	V _{EB} = 5V, I _C = 0	_	_	100	nA
DC current gain		h _{FE}	_	V _{CE} = 5V, I _C = 1mA	120	_	700	_
Collector-emitter saturation voltage		V _{CE (sat)}	_	I _C = 5mA, I _B = 0.25mA	_	0.1	0.3	V
Translation frequency		f _T	_	V _{CE} = 10V, I _C = 5mA	_	250	_	MHz
Collector output capacitance		C _{ob}	_	V _{CB} = 10V, I _E = 0, f = 1MHz	_	3	6	pF
Input resistor	RN1970	- R1	_	_	3.29	4.7	6.11	kΩ
	RN1971				7	10	13	

(Q1, Q2 Common)



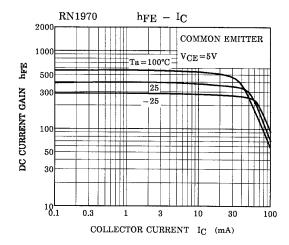


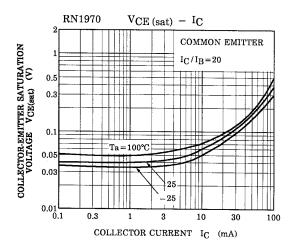


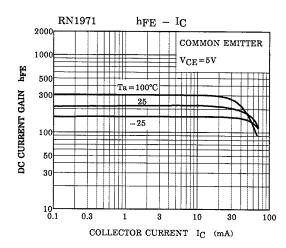


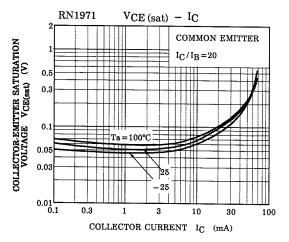
3 2005-02-22

(Q1, Q2 Common)











Type Name	Marking	
RN1970	Type Name XXK	
RN1971	Type Name XXM HHH	

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